B-Suffix Series CMOS Gates

MC14001B, MC14011B, MC14023B, MC14025B, MC14071B, MC14073B, MC14081B, MC14082B

The B Series logic gates are constructed with P and N channel enhancement mode devices in a single monolithic structure (Complementary MOS). Their primary use is where low power dissipation and/or high noise immunity is desired.

Features

- Supply Voltage Range = 3.0 Vdc to 18 Vdc
- All Outputs Buffered
- Capable of Driving Two Low-power TTL Loads or One Low-power Schottky TTL Load Over the Rated Temperature Range.
- Double Diode Protection on All Inputs Except: Triple Diode Protection on MC14011B and MC14081B
- Pin-for-Pin Replacements for Corresponding CD4000 Series B Suffix Devices
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

MAXIMUM RATINGS (Voltages Referenced to V_{SS})

Symbol	Parameter	Value	Unit
V_{DD}	DC Supply Voltage Range	-0.5 to +18.0	V
V _{in} , V _{out}	Input or Output Voltage Range (DC or Transient)	-0.5 to V _{DD} + 0.5	V
I _{in} , I _{out}	Input or Output Current (DC or Transient) per Pin	±10	mA
P _D	Power Dissipation, per Package (Note 1)	500	mW
T _A	Ambient Temperature Range	-55 to +125	°C
T _{stg}	Storage Temperature Range	-65 to +150	°C
TL	Lead Temperature (8–Second Soldering)	260	°C
V _{ESD}	ESD Withstand Voltage Human Body Model Machine Model Charged Device Model	> 3000 > 300 N/A	V

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Temperature Derating: "D/DW" Packages: -7.0 mW/°C From 65°C To 125°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range $V_{SS} \leq (V_{in} \text{ or } V_{out}) \leq V_{DD}.$

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either V_{SS} or V_{DD}). Unused outputs must be left open.



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SOIC-14 D SUFFIX CASE 751A TSSOP-14 DT SUFFIX CASE 948G

MARKING DIAGRAMS





SOIC-14

TSSOP-14

xx = Specific Device Code A = Assembly Location

WL, L = Wafer Lot YY, Y = Year WW, W = Work Week G or ■ = Pb-Free Package

(Note: Microdot may be in either location)

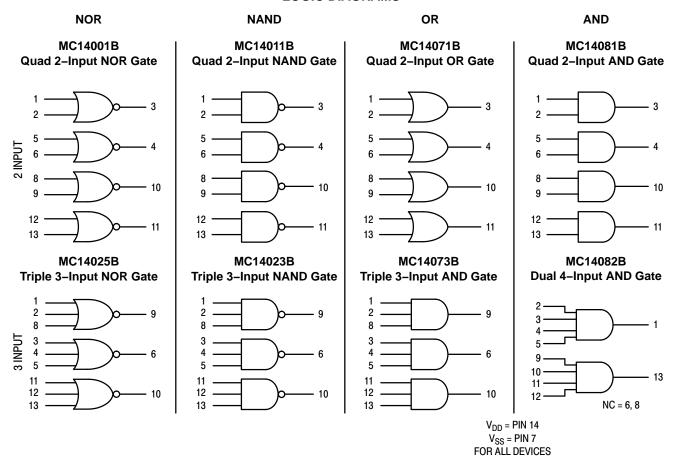
DEVICE INFORMATION

Device	Description
MC14001B	Quad 2-Input NOR Gate
MC14011B	Quad 2-Input NAND Gate
MC14023B	Triple 3-Input NAND Gate
MC14025B	Triple 3-Input NOR Gate
MC14071B	Quad 2-Input OR Gate
MC14073B	Triple 3-Input AND Gate
MC14081B	Quad 2-Input AND Gate
MC14082B	Dual 4-Input AND Gate

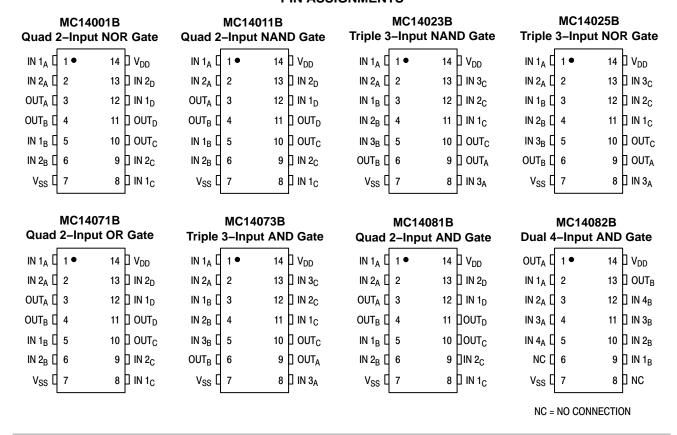
ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 8 of this data sheet.

LOGIC DIAGRAMS



PIN ASSIGNMENTS



ELECTRICAL CHARACTERISTICS (Voltages Referenced to V_{SS})

				- 5	5°C		25°C		125	5°C	
Characteristic		Symbol	V _{DD} Vdc	Min	Max	Min	Typ (Note 2)	Max	Min	Max	Unit
Output Voltage V _{in} = V _{DD} or 0	"0" Level	V _{OL}	5.0 10 15	- - -	0.05 0.05 0.05	- - -	0 0 0	0.05 0.05 0.05	_ _ _	0.05 0.05 0.05	Vdc
$V_{in} = 0$ or V_{DD}	"1" Level	V _{OH}	5.0 10 15	4.95 9.95 14.95		4.95 9.95 14.95	5.0 10 15		4.95 9.95 14.95	- - -	Vdc
Input Voltage ($V_O = 4.5 \text{ or } 0.5 \text{ Vdc}$) ($V_O = 9.0 \text{ or } 1.0 \text{ Vdc}$) ($V_O = 13.5 \text{ or } 1.5 \text{ Vdc}$)	"0" Level	V _{IL}	5.0 10 15	- - -	1.5 3.0 4.0	_ _ _	2.25 4.50 6.75	1.5 3.0 4.0	- - -	1.5 3.0 4.0	Vdc
$(V_O = 0.5 \text{ or } 4.5 \text{ Vdc})$ $(V_O = 1.0 \text{ or } 9.0 \text{ Vdc})$ $(V_O = 1.5 \text{ or } 13.5 \text{ Vdc})$	"1" Level	V _{IH}	5.0 10 15	3.5 7.0 11	- - -	3.5 7.0 11	2.75 5.50 8.25	- - -	3.5 7.0 11	- - -	Vdc
Output Drive Current $(V_{OH} = 2.5 \text{ Vdc})$ $(V_{OH} = 4.6 \text{ Vdc})$ $(V_{OH} = 9.5 \text{ Vdc})$ $(V_{OH} = 13.5 \text{ Vdc})$	Source	I _{OH}	5.0 5.0 10 15	-3.0 -0.64 -1.6 -4.2	- - -	-2.4 -0.51 -1.3 -3.4	-4.2 -0.88 -2.25 -8.8	- - -	-1.7 -0.36 -0.9 -2.4	- - -	mAdc
$(V_{OL} = 0.4 \text{ Vdc})$ $(V_{OL} = 0.5 \text{ Vdc})$ $(V_{OL} = 1.5 \text{ Vdc})$	Sink	I _{OL}	5.0 10 15	0.64 1.6 4.2	- - -	0.51 1.3 3.4	0.88 2.25 8.8	- - -	0.36 0.9 2.4	- - -	mAdc
Input Current		I _{in}	15	_	±0.1	_	±0.00001	±0.1	_	±1.0	μAdc
Input Capacitance (V _{in} = 0)		C _{in}	-	-	-	-	5.0	7.5	-	-	pF
Quiescent Current (Per Package)		I _{DD}	5.0 10 15	- - -	0.25 0.5 1.0	- - -	0.0005 0.0010 0.0015	0.25 0.5 1.0	- - -	7.5 15 30	μAdc
Total Supply Current (Note (Dynamic plus Quiesce Per Gate, C _L = 50 pF)		I _T	5.0 10 15		1	$I_{T} = (0.$	3 μA/kHz) f - 6 μA/kHz) f - 9 μA/kHz) f -	+ I _{DD} /N		1	μAdc

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

- Data labelled "Typ" is not to be used for design purposes but is intended as an indication of the IC's potential performance.
 The formulas given are for the typical characteristics only at 25°C.
- 4. To calculate total supply current at loads other than 50 pF:

$$I_T(C_L) = I_T(50 \text{ pF}) + (C_L - 50) \text{ Vfk}$$

where: I_T is in μA (per package), C_L in pF, $V = (V_{DD} - V_{SS})$ in volts, f in kHz is input frequency, and k = 0.001 x the number of exercised gates per package.

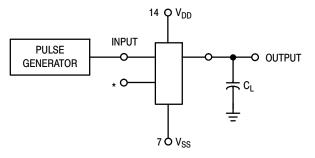
B-SERIES GATE SWITCHING TIMES

SWITCHING CHARACTERISTICS (Note 5) ($C_L = 50 \text{ pF}, T_A = 25^{\circ}\text{C}$)

Characteristic	Symbol	V _{DD} Vdc	Min	Typ (Note 6)	Max	Unit
Output Rise Time, All B-Series Gates	t _{TLH}					ns
$t_{TLH} = (1.35 \text{ ns/pF}) C_L + 33 \text{ ns}$		5.0	_	100	200	
$t_{TLH} = (0.60 \text{ ns/pF}) C_L + 20 \text{ ns}$		10	_	50	100	
$t_{TLH} = (0.40 \text{ ns/PF}) C_L + 20 \text{ ns}$		15	_	40	80	
Output Fall Time, All B-Series Gates	t _{THL}					ns
$t_{THL} = (1.35 \text{ ns/pF}) C_L + 33 \text{ ns}$		5.0	_	100	200	
$t_{THL} = (0.60 \text{ ns/pF}) C_L + 20 \text{ ns}$		10	_	50	100	
$t_{THL} = (0.40 \text{ ns/pF}) C_L + 20 \text{ ns}$		15	_	40	80	
Propagation Delay Time	t _{PLH} , t _{PHL}					ns
MC14001B, MC14011B only						
t_{PLH} , $t_{PHL} = (0.90 \text{ ns/pF}) C_L + 80 \text{ ns}$		5.0	_	125	250	
t_{PLH} , $t_{PHL} = (0.36 \text{ ns/pF}) C_L + 32 \text{ ns}$		10	_	50	100	
t_{PLH} , $t_{PHL} = (0.26 \text{ ns/pF}) C_L + 27 \text{ ns}$		15	_	40	80	
All Other 2, 3, and 4 Input Gates						
t_{PLH} , $t_{PHL} = (0.90 \text{ ns/pF}) C_L + 115 \text{ ns}$		5.0	_	160	300	
t_{PLH} , $t_{PHL} = (0.36 \text{ ns/pF}) C_L + 47 \text{ ns}$		10	_	65	130	
t_{PLH} , $t_{PHL} = (0.26 \text{ ns/pF}) C_L + 37 \text{ ns}$		15	_	50	100	
8-Input Gates (MC14068B, MC14078B)						
t_{PLH} , $t_{PHL} = (0.90 \text{ ns/pF}) C_L + 155 \text{ ns}$		5.0	_	200	350	
t_{PLH} , $t_{PHL} = (0.36 \text{ ns/pF}) C_L + 62 \text{ ns}$		10	_	80	150	
t_{PLH} , $t_{PHL} = (0.26 \text{ ns/pF}) C_L + 47 \text{ ns}$		15	_	60	110	

^{5.} The formulas given are for the typical characteristics only at 25°C.

^{6.} Data labelled "Typ" is not to be used for design purposes but is intended as an indication of the IC's potential performance.



^{*}All unused inputs of AND, NAND gates must be connected to V_{DD} . All unused inputs of OR, NOR gates must be connected to V_{SS} .

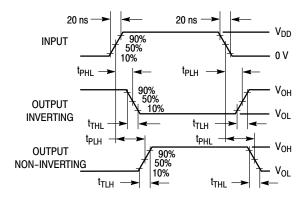
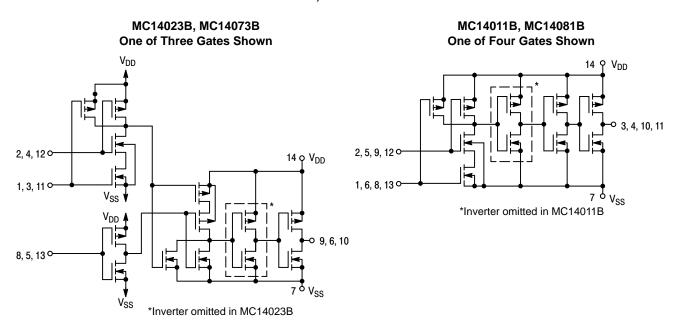


Figure 1. Switching Time Test Circuit and Waveforms

CIRCUIT SCHEMATIC NOR, OR GATES

MC14001B, MC14071B MC14025B One of Four Gates Shown One of Three Gates Shown 14 9 V_{DD} 1, 3, 11 0 1, 6, 8, 13 o-2, 4, 12 0 2, 5, 9, 12 0-14 9 V_{DD} 0 3, 4, 10, 11 V_{SS} o 9, 6, 10 V_{SS} V_{DD} ♠ *Inverter omitted in MC14001B 8, 5, 13 0 *Inverter omitted in MC14025B

CIRCUIT SCHEMATIC NAND, AND GATES



TYPICAL B-SERIES GATE CHARACTERISTICS

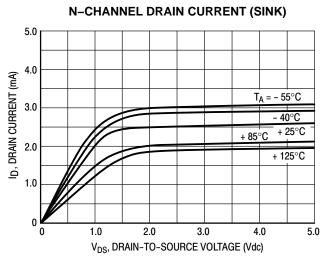


Figure 2. V_{GS} = 5.0 Vdc

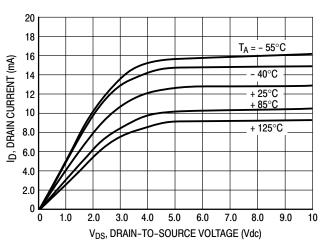


Figure 4. V_{GS} = 10 Vdc

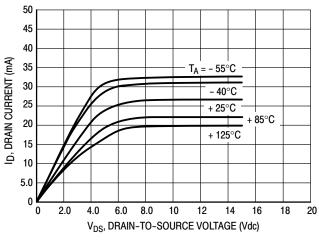


Figure 6. V_{GS} = 15 Vdc

P-CHANNEL DRAIN CURRENT (SOURCE) - 10 - 9.0 - 8.0 $T_A = -55^{\circ}C$ ID, DRAIN CURRENT (mA) - 7.0 - 6.0 - 5.0 + 25°C - 85°C - 4.0 125°C - 3.0 - 2.0 - 1.0 - 1.0 - 2.0 - 3.0 - 5.0 V_{DS}, DRAIN-TO-SOURCE VOLTAGE (Vdc)

Figure 3. $V_{GS} = -5.0 \text{ Vdc}$

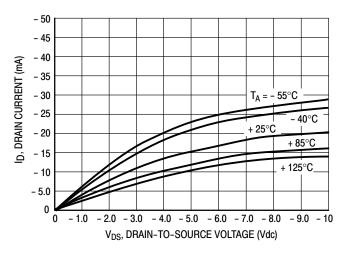


Figure 5. $V_{GS} = -10 \text{ Vdc}$

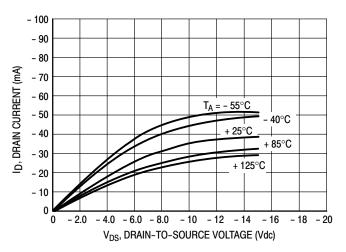


Figure 7. $V_{GS} = -15 \text{ Vdc}$

These typical curves are not guarantees, but are design aids. Caution: The maximum rating for output current is 10 mA per pin.

TYPICAL B-SERIES GATE CHARACTERISTICS (cont'd)

VOLTAGE TRANSFER CHARACTERISTICS

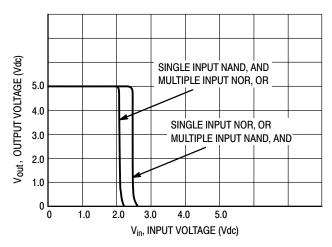


Figure 8. $V_{DD} = 5.0 \text{ Vdc}$

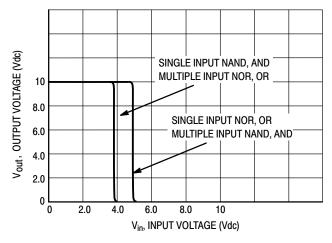


Figure 9. $V_{DD} = 10 \text{ Vdc}$

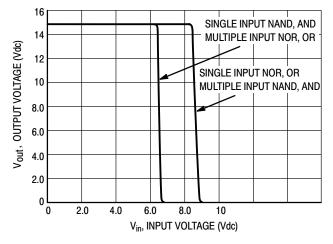


Figure 10. $V_{DD} = 15 \text{ Vdc}$

DC NOISE MARGIN

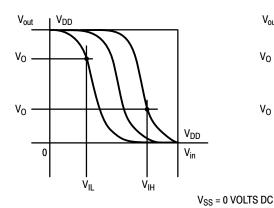
The DC noise margin is defined as the input voltage range from an ideal "1" or "0" input level which does not produce output state change(s). The typical and guaranteed limit values of the input values V_{IL} and V_{IH} for the output(s) to be at a fixed voltage V_O are given in the Electrical Characteristics table. V_{IL} and V_{IH} are presented graphically in Figure 11.

Guaranteed minimum noise margins for both the "1" and "0" levels =

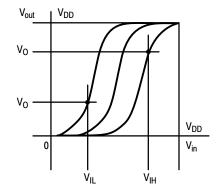
1.0 V with a 5.0 V supply

2.0 V with a 10.0 V supply

2.5 V with a 15.0 V supply



(a) Inverting Function



(b) Non-Inverting Function

Figure 11. DC Noise Immunity

ORDERING INFORMATION

Device	Package	Shipping [†]	
MC14001BDG	SOIC-14	55 Heite / Deit	
NLV14001BDG*	(Pb-Free)	55 Units / Rail	
MC14001BDR2G	SOIC-14		
NLV14001BDR2G*	(Pb-Free)	OFOO Haite / Tana 9 Back	
MC14001BDTR2G	TSSOP-14	2500 Units / Tape & Reel	
NLV14001BDTR2G*	(Pb-Free)		
MC14001BFELG	SOEIAJ-14 (Pb-Free)	2000 Units / Tape & Reel	
MC14011BDG	SOIC-14	55 Heire / Deill	
NLV14011BDG*	(Pb-Free)	55 Units / Rail	
MC14011BDR2G	SOIC-14		
NLV14011BDR2G*	(Pb-Free)		
MC14011BDTR2G	TSSOP-14	2500 Units / Tape & Reel	
NLV14011BDTR2G*	(Pb-Free)		
MC14011BFG	SOEIAJ-14	50 Units / Rail	
MC14011BFELG	(Pb-Free)	2000 Units / Tape & Reel	
MC14023BDG	SOIC-14 (Pb-Free)	55 Units / Rail	
MC14023BDR2G	SOIC-14	2500 Units / Tape & Reel	
NLV14023BDR2G*	(Pb-Free)	2500 Offits / Tape & Reef	
MC14023BFELG	SOEIAJ-14 (Pb-Free)	2000 Units / Tape & Reel	
MC14025BDG	SOIC-14		
NLV14025BDG*	(Pb-Free)	55 Units / Rail	
MC14025BDR2G	SOIC-14		
NLV14025BDR2G*	(Pb–Free)	2500 Units / Tape & Reel	
MC14071BDG	SOIC-14	55 Units / Rail	
NLV14071BDG*	(Pb-Free)	33 Offits / Naii	
MC14071BDR2G	SOIC-14	2500 Units / Tape & Reel	
NLV14071BDR2G*	(Pb-Free)	2000 Offits / Tape & Reel	
MC14071BDTG		96 Units per Rail	
MC14071BDTR2G	TSSOP-14 (Pb-Free)	2500 Unite / Tana & Page	
NLV14071BDTR2G*	, , ,	2500 Units / Tape & Reel	
MC14073BDG	SOIC-14 (Pb-Free)	55 Units / Rail	
MC14073BDR2G	SOIC-14 (Pb-Free)	2500 Units / Tape & Reel	

ORDERING INFORMATION (continued)

Device	Package	Shipping [†]	
MC14081BDG	SOIC-14	55 Heite / Deil	
NLV14081BDG*	(Pb-Free)	55 Units / Rail	
MC14081BDR2G	SOIC-14		
NLV14081BDR2G*	(Pb-Free)	050011 % (7 0 0 0 1	
MC14081BDTR2G	TSSOP-14	2500 Units / Tape & Reel	
NLV14081BDTR2G*	(Pb-Free)		

MC14082BDG		EE Unito / Doil
NLV14082BDG*	SOIC-14 (Pb-Free)	55 Units / Rail
MC14082BDR2G	` ,	2500 Units / Tape & Reel

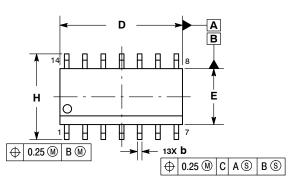
[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

^{*}NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q100 Qualified and PPAP Capable.



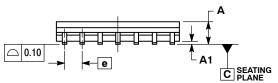
SOIC-14 NB CASE 751A-03 ISSUE L

DATE 03 FEB 2016









MILLIMETERS DIM MIN MAX MIN MAX A 1.35 1.75 0.054 0.068

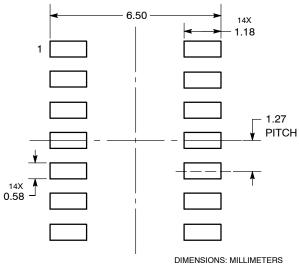
A1	0.10	0.25	0.004	0.010	
АЗ	0.19	0.25	0.008	0.010	
b	0.35	0.49	0.014	0.019	
D	8.55	8.75	0.337	0.344	
Е	3.80	4.00	0.150	0.157	
е	1.27	BSC	0.050 BSC		
Н	5.80	6.20	0.228	0.244	
h	0.25	0.50	0.010	0.019	
L	0.40	1.25	0.016	0.049	
М	0 °	7°	0 °	7°	

5. MAXIMUM MOLD PROTRUSION 0.15 PER

NOTES:
1. DIMENSIONING AND TOLERANCING PER

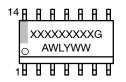
ASME Y14.5M, 1994.
CONTROLLING DIMENSION: MILLIMETERS. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF AT MAXIMUM MATERIAL CONDITION.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSIONS.

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC MARKING DIAGRAM*



XXXXX = Specific Device Code Α = Assembly Location

WL = Wafer Lot Υ = Year = Work Week WW G = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator. "G" or microdot " ■". may or may not be present.

STYLES ON PAGE 2

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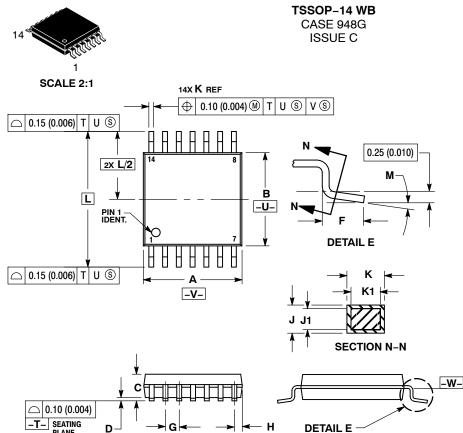
SOIC-14 CASE 751A-03 ISSUE L

DATE 03 FEB 2016

STYLE 1: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. NO CONNECTION 5. ANODE/CATHODE 6. NO CONNECTION 7. ANODE/CATHODE 8. ANODE/CATHODE 9. ANODE/CATHODE 10. NO CONNECTION 11. ANODE/CATHODE 12. ANODE/CATHODE 13. NO CONNECTION 14. COMMON ANODE	STYLE 2: CANCELLED	STYLE 3: PIN 1. NO CONNECTION 2. ANODE 3. ANODE 4. NO CONNECTION 5. ANODE 6. NO CONNECTION 7. ANODE 8. ANODE 9. ANODE 10. NO CONNECTION 11. ANODE 12. ANODE 13. NO CONNECTION 14. COMMON CATHODE	STYLE 4: PIN 1. NO CONNECTION 2. CATHODE 3. CATHODE 4. NO CONNECTION 5. CATHODE 6. NO CONNECTION 7. CATHODE 8. CATHODE 9. CATHODE 10. NO CONNECTION 11. CATHODE 12. CATHODE 13. NO CONNECTION 14. COMMON ANODE
STYLE 5: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. ANODE/CATHODE 5. ANODE/CATHODE 6. NO CONNECTION 7. COMMON ANODE 8. COMMON CATHODE 9. ANODE/CATHODE 10. ANODE/CATHODE 11. ANODE/CATHODE 12. ANODE/CATHODE 13. NO CONNECTION 14. COMMON ANODE	STYLE 6: PIN 1. CATHODE 2. CATHODE 3. CATHODE 4. CATHODE 5. CATHODE 6. CATHODE 7. CATHODE 8. ANODE 9. ANODE 10. ANODE 11. ANODE 12. ANODE 13. ANODE 14. ANODE	STYLE 7: PIN 1. ANODE/CATHODE 2. COMMON ANODE 3. COMMON CATHODE 4. ANODE/CATHODE 5. ANODE/CATHODE 6. ANODE/CATHODE 7. ANODE/CATHODE 8. ANODE/CATHODE 9. ANODE/CATHODE 10. ANODE/CATHODE 11. COMMON CATHODE 12. COMMON ANODE 13. ANODE/CATHODE 14. ANODE/CATHODE	STYLE 8: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. NO CONNECTION 5. ANODE/CATHODE 6. ANODE/CATHODE 7. COMMON ANODE 8. COMMON ANODE 9. ANODE/CATHODE 10. ANODE/CATHODE 11. NO CONNECTION 12. ANODE/CATHODE 13. ANODE/CATHODE 14. COMMON CATHODE

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DATE 17 FEB 2016

- NOTES.

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

 2. CONTROLLING DIMENSION: MILLIMETER.

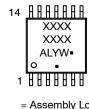
 3. DIMENSION A DOES NOT INCLUDE MOLD
- FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
 DIMENSION B DOES NOT INCLUDE
- INTERLEAD FLASH OR PROTRUSION.
 INTERLEAD FLASH OR PROTRUSION SHALL
- INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.

 5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.

 6. TERMINAL NUMBERS ARE SHOWN FOR DEFERENCE ONLY
- REFERENCE ONLY.
 DIMENSION A AND B ARE TO BE
- DETERMINED AT DATUM PLANE -W-.

	MILLIMETERS		INC	HES
DIM	MIN	MAX	MIN	MAX
Α	4.90	5.10	0.193	0.200
В	4.30	4.50	0.169	0.177
С		1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65	BSC	0.026 BSC	
Н	0.50	0.60	0.020	0.024
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40	BSC	0.252	BSC
М	o°	8 °	0 °	8 °

GENERIC MARKING DIAGRAM*



= Assembly Location

= Wafer Lot ٧ = Year

W = Work Week

= Pb-Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

1	
14X 0.36	DIMENSIONS: MILLIMETERS

SOLDERING FOOTPRINT

7.06

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